

MK48T85Q

ADDRESS / DATA MULTIPLEX TIMEKEEPER™ RAM

PIN CONNECTIONS

ADVANCE DATA

- DROP-IN REPLACEMENT FOR IBM AT COM-PUTER CLOCK/CALENDAR
- PIN COMPATIBLE WITH THE DS1285Q
- EXTERNAL BATTERY AND CRYSTAL PINS
- COUNTS SECONDS, MINUTES, HOURS, DAYS, DAY OF THE WEEK, DATE, MONTH AND YEAR WITH LEAP YEAR COMPENSA-TION
- BINARY OR BCD REPRESENTATION OF TI-ME, CALENDAR AND ALARM
- 12 OR 24 HOUR CLOCK WITH AM AND PM IN 12 HOUR MODE
- SELECTABLE BETWEEN MOTOROLA AND IN-TEL BUS TIMING
- MULTIPLEX BUS FOR PIN EFFICIENCY
- INTERFACED WITH SOFTWARE AS 64 RAM LOCATIONS

14 bytes of clock and control registers

50 bytes of general purpose ram

- PROGRAMMABLE SQUARE WAVE OUTPUT SIGNAL
- BUS COMPATIBLE INTERRUPT SIGNALS (IRQ)
- THREE INTERRUPTS ARE SEPARATELY SOFTWARE-MASKABLE AND TESTABLE

Time-of-day alarm once/second to once/day

Periodic rates from 122 us to 500 ms

End of clock update cycle



PIN NAMES

A/D0 - A/D7	ADDRESS / DATA		
MOT	BUS TYPE SELECTION		
E	CHIP SELECT		
AS	ADDRESS STROBE		
W	READ / WRITE		
SQW	SQUARE WAVE OUT		
IRQ	INTERRUPT REQUEST		
RESET	RESET		
DS	DATA STROBE		
Vcc	+5 VOLTS		
GND	GROUND		
RCLR	RAM CLEAR		
X1, X2	32.768 KHz CRYSTAL		
VBAT	+3 VOLT BATTERY INPUT		
NF*	NO FUNCTION		

* This pin serves no function and may be connected to other signals without affecting device operation. The electrical characteristics are the same as the other inputs pins.

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DESCRIPTION

The MK48T85 RealTime Clock and RAM is designed to be a functional replacement for the DS1285. The functions available to the user include a time-of-day clock, an alarm, a one-hundred-year calendar, programmable interrupts, a square wave generator, and 50 bytes of static RAM. The MK48T85 provides connections for a battery and a 32.768 KHz crystal. The battery connection allows the user to back-up the RAM and clock functions in the absence of system voltage.

Automatic deselection of the device provides insurance that data integrity is not compromised should V_{CC} fall below specified (V_{PFD}) levels. The automatic deselection of the device remains in effect upon power up for a period of 100ms after V_{CC} rises above V_{PFD}, provided the Real Time Clock is running and the count down chain is not in reset, allowing sufficient time for V_{CC} to stabilize and giving the system clock a wake up period so that a valid system reset can be established.

OPERATION

The block diagram in Figure 1 shows the pin connection with the major functions of MK48T85 (Real Time Clock/RAM). For a complete description of operating conditions, electrical characteristics, bus timing, and pin descriptions other than X1, X2, VBAT, and RCLR see the MK48T87(B) datasheet.



FIGURE 1 . BLOCK DIAGRAM



SIGNAL DESCRIPTIONS

X1, X2 - The X1 and X2 pins are the connections for a standard 32.768 KHz quartz crystal.

VBAT - The VBAT pin is the battery input for any standard 3V lithium cell or other energy source.

RCLR - the RCLR pin is used to clear (set to logic "1") all 50 bytes of the general purpose RAM associated with the Real Time Clock. In or-

der to clear the RAM, RCLR must be forced to an input logic "0" (-0.3 to 0.8 volts) for a minimun of 100 ms when VCC is applied

FOR COMPLETE DESCRIPTION OF OPERA-TING CONDITIONS, ELECTRICAL CHARAC-TERISTICS. BUS TIMING, PACKAGE DIMEN-SION, AND PIN DESCRIPTIONS, SEE THE MK48T87(B) DATASHEET.

DC ELECTRICAL CHARACTERISTICS (0 C \leq T_A \leq 70 C) (V_{CC (Max)} \leq V_{CC} \leq V_{CC(Min)})

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
lcci	Average V _{CC} Power Supply Current		15	mA	
mot	Input Current	-1.0	500	μΑ	
hL.	Input Leakage Current	-1	+1	μA	
IOL	Output Leakage Current	-5	+5	μΑ	
VOH	Output Logic "1" Voltage (Iour = -1.0 mA)	2.4		V	
Vol	Output Logic "0" Voltage (IOUT = 4.0 mA)		0.4	V	
VBAT	Battery Voltage	2.4	3.5	V	

CRYSTAL ELECTRICAL CHARACTERISTICS (externally supplied)

SYMBOL	PARAMETER	TEST CONDITIONS	VALUES			LINITS
STMBOL		TEST CONDITIONS	MIN	TYP	MAX	UNITS
fo	Resonant Frequancy			32.768		KHz
rs	Series Resistance				30	KΩ
CL	load Capacitance		12.5			pf



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FIGURE 2 . POWER-UP / POWER-DOWN CONDITIONS



AC ELECTRICAL CHARACTERISTICS (POWER-UP / DOWN TIMING)

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
tep	E or W at VIH Before Power Down	0		ns	
tr	VPFD to Vso Vcc Fall Time	310		μs	
tR	V _{SO} to V _{PFD} V _{CC} Rise Time	100		μs	

DC ELECTRICAL CHARACTERISTICS (POWER-UP/ DOWN TRIP POINTS)(0 C \leq T_A \leq 70 C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	NOTES
VPFD	Power-fail Deselect Voltage		1.29 VBAT		V	
Vso	Battery Back-up Swithover Voltage		VBAT		V	





DIM	INC	INCHES		
DIM	MIN	MAX	NOTES	
A	0.165	0.185	2	
A1	0.090	0.120	2	
В	0.026	0.032	2	
B1	0.013	0.021	2	
D	0.485	0.495		
D1	0.450	0.456		
D2	0.390	0.430		
E	0.485	0.495		
E1	0.450	0.456		
E2	0.390	0.430		
h	0.042	0.060		
j	0.042	0.060		
k	0.042	0.056		

NOTES:

1. Lead finish to be solder dip or tin/lead plate.

2. The maximun limit shall be increased by 0.003 inche when solder lead finish is specified.

